TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOSIV)

TPCA8026

Lithium-Ion Battery Applications Notebook PC Applications Portable Equipment Applications

- Small footprint due to a small and thin package
- Low drain-source ON-resistance: $RDS(ON) = 1.8 \text{ m}\Omega \text{ (typ.)}$
- High forward transfer admittance: $|Y_{fs}| = 100 \text{ S (typ.)}$
- Low leakage current: $IDSS = 10 \mu A (max) (VDS = 30 V)$
- Enhancement mode: $V_{th} = 1.3$ to 2.5 V ($V_{DS} = 10$ V, $I_{D} = 1$ mA)

Absolute Maximum Ratings (Ta = 25°C)

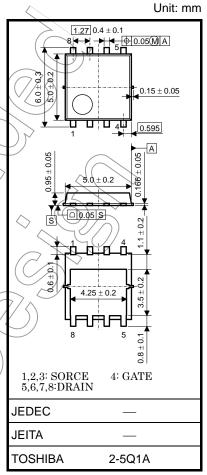
Characteristic		Symbol	Rating	Unit		
Drain-source voltage		V_{DSS}	30	V		
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V _{DGR}	30	X		
Gate-source voltage		V _{GSS}	±20	/ (v		
Drain current	DC (Note 1)	ID	45	A		
	Pulsed (Note 1)	IDP	135	A \		
Drain power dissipation	on (Tc = 25°C)	(PD \	45	\ w		
Drain power dissipation	on (t = 10 s) (Note 2a)	PD	2.8	W		
Drain power dissipation	on (t = 10 s) (Note 2b)	PD	(1.6/ \)	W		
Single-pulse avalanche energy (Note 3)		EAS	263	mJ		
Avalanche current		I _{AR}	45	Α		
Repetitive avalanche energy (Tc = 25°C) (Note 4)		EAR	3.4	mJ		
Channel temperature		Tch	150	°C		
Storage temperature range		T _{stg}	-55 to 150	°C		

Note: For Notes 1 to 4, refer to the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating

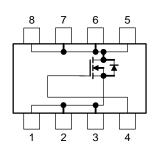
Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.



Weight: 0.069 g (typ.)

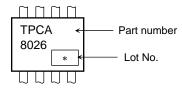
Circuit Configuration



Thermal Characteristics

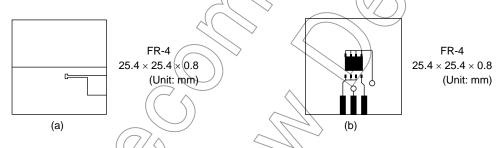
Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case $(\mbox{Tc} = 25\mbox{°C}) \label{eq:Tc}$	R _{th (ch-c)}	2.78	°C/W
Thermal resistance, channel to ambient $(t = 10 \text{ s})$ (Note 2a)	R _{th (ch-a)}	44.6	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R _{th (ch-a)}	78.1	°C/W

Marking (Note 5)



Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (b) Device mounted on a glass-epoxy board (b)



Note 3: $V_{DD} = 24 \text{ V}$, $T_{Ch} = 25^{\circ}\text{C}$ (initial), L = 0.1 mH, $AR \neq 45 \text{ A}$

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: * Weekly code: (Three digits)

Week of manufacture

(01) for the first week of the year, continuing up to 52 or 53)

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Year of manufacture

(The last digit of the year)

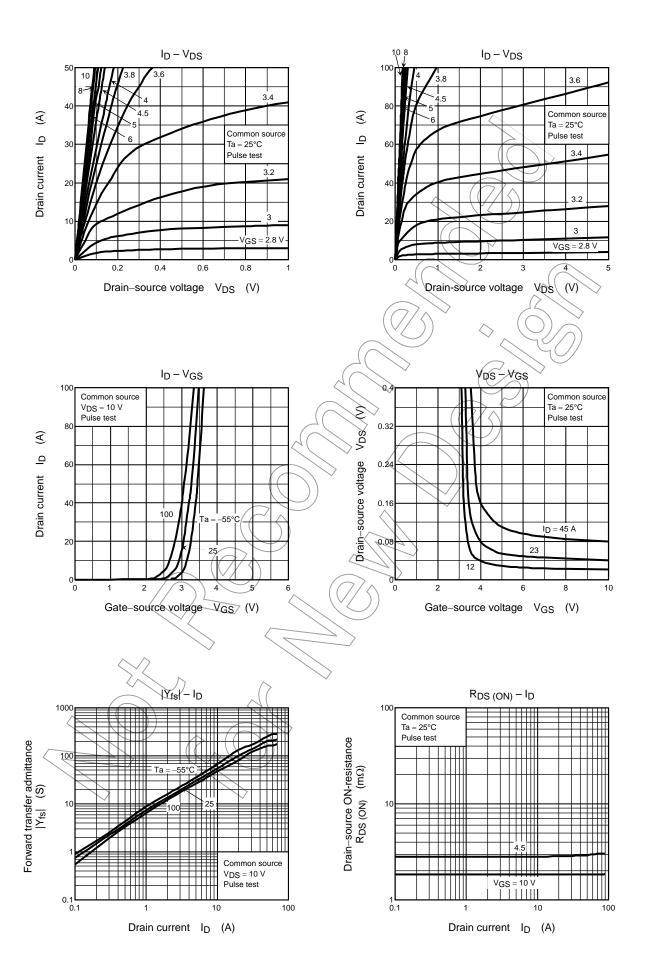
Electrical Characteristics (Ta = 25°C)

Ch	aracteristic	Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage cur	rent	I _{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±100	nA	
Drain cutoff curre	ent	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	_	_	10	μА	
Drain-source breakdown voltage		V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	30	_	_	V	
		V (BR) DSX	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	10	_	_		
Gate threshold vo	oltage	V_{th}	V _{DS} = 10 V, I _D = 1 mA	1.3) >_	2.5	V	
Drain-source ON-resistance		D	V _{GS} = 4.5 V, I _D = 23 A	<u> </u>	2.7	4.5	- mΩ	
		R _{DS} (ON)	V _{GS} = 10 V, I _D = 23 A))	1.8	2.2		
Forward transfer	admittance	Y _{fs}	V _{DS} = 10 V, I _D = 23 A	50	100	_	S	
Input capacitance		C _{iss}		² —	4200	_		
Reverse transfer capacitance		C _{rss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	1000	_	pF	
Output capacitan	се	C _{oss}			1400	7		
Switching time	Rise time	t _r	V _{GS} 10 V	-(15	> _		
	Turn-on time	t _{on}		VGS 0V VOUT	_			
	Fall time	t _f	R = 0.6		36	_	ns	
	Turn-off time	t _{off}	V _{DD} ≈ 15 V Duty ≤ 1%, t _W = 10 μs) —	111	_		
Total gate charge (gate-source plus		Qg		_	113			
Gate-source charge 1		Q _{gs1}	$V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 45 \text{ A}$	_	13	_	nC	
Gate-drain ("miller") charge		Qgd		_	42	_		

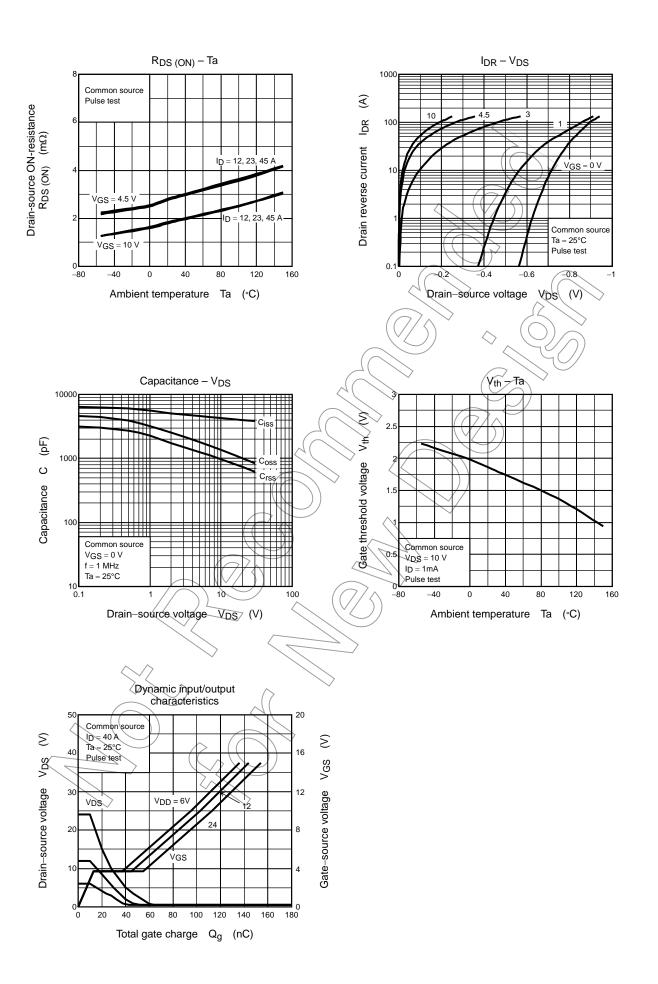
Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Drain reverse current Pulse (Note-1)	I _{DRP}	_	_	_	135	Α
Forward voltage (diode)	VDSF	$I_{DR} = 45 \text{ A}, V_{GS} = 0 \text{ V}$	_	_	-1.2	V

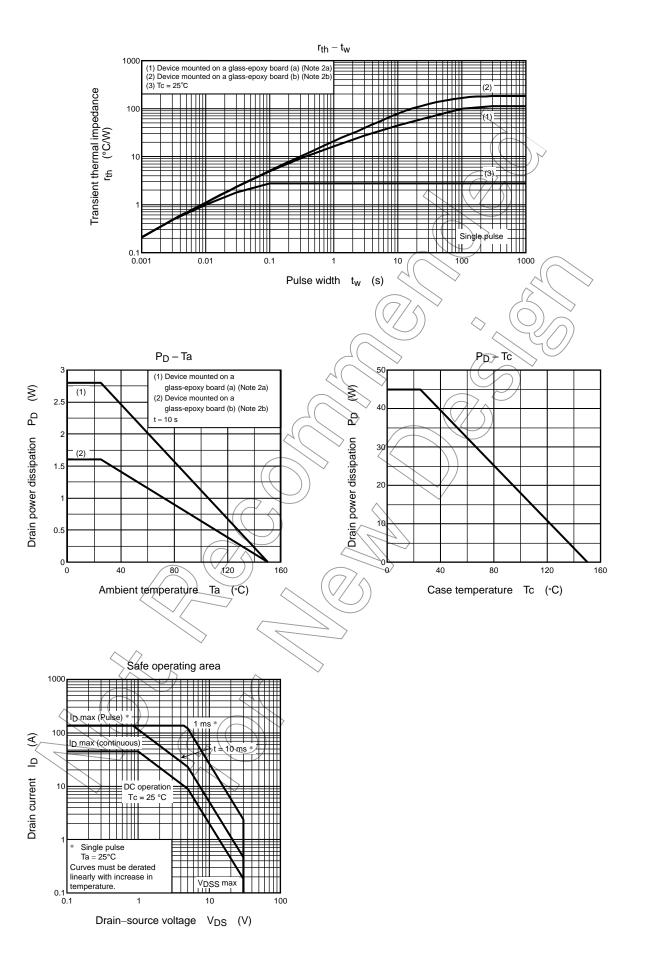




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